

## Silicon PNP Power Transistors

## 2SA636 2SA636A

## DESCRIPTION

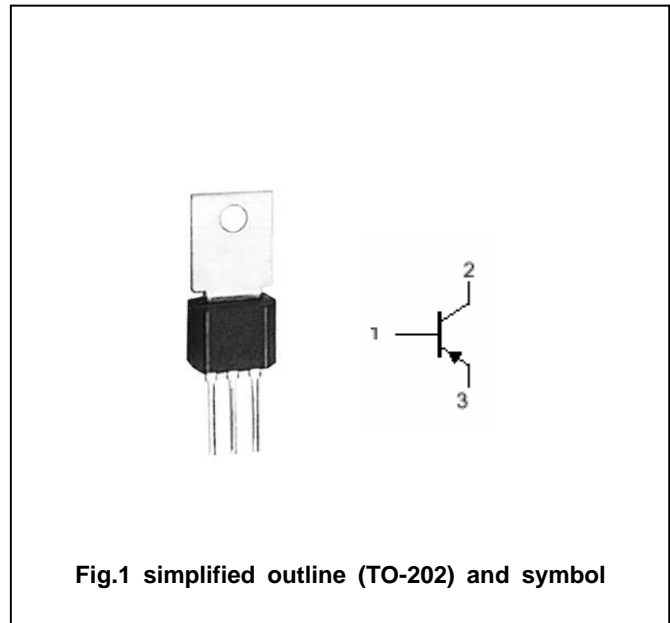
- With TO-202 package
- Complement to type 2SC1098/1098A
- High breakdown voltage
- High transition frequency

## APPLICATIONS

- For audio frequency power amplifier and low speed switching applications

## PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



## Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	-70	V
$V_{CEO}$	Collector-emitter voltage	2SA636	-45	V
		2SA636A	-60	
$V_{EBO}$	Emitter-base voltage	Open collector	-5	V
$I_C$	Collector current		-3	A
$I_{CM}$	Collector current-peak		-5	A
$I_B$	Base current		-0.6	A
$P_T$	Total power dissipation	$T_C=25^\circ\text{C}$	10	W
		$T_a=25^\circ\text{C}$	1.2	
$T_j$	Junction temperature		150	$^\circ\text{C}$
$T_{stg}$	Storage temperature		-55~150	$^\circ\text{C}$

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-1.5A ; I <sub>B</sub> =-0.15A		-0.5	-2.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =-1.5A ; I <sub>B</sub> =-0.15A		-0.8	-2.0	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =-45V; I <sub>E</sub> =0			-1	μ A
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-3V; I <sub>C</sub> =0			-1	μ A
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =-20mA ; V <sub>CE</sub> =-5V	20			
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =-0.5A ; V <sub>CE</sub> =-5V	40		250	
C <sub>OB</sub>	Output capacitance	I <sub>E</sub> =0; V <sub>CB</sub> =-10V; f=1MHz		60		pF
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =-0.1A ; V <sub>CB</sub> =-5V		45		MHz

◆ h<sub>FE-2</sub> classifications

N	M	L	K
40-60	50-100	80-160	120-250

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PACKAGE OUTLINE

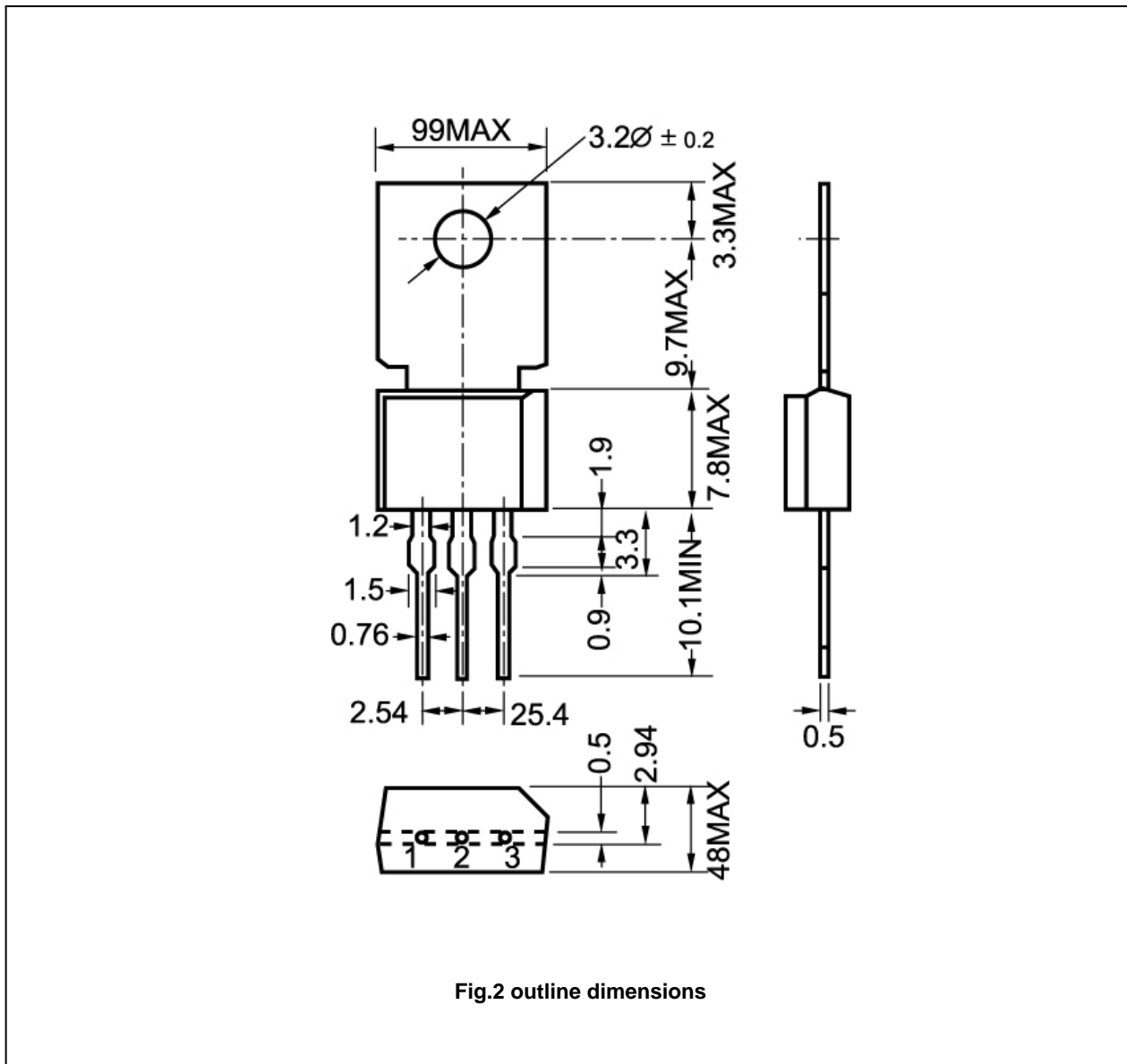


Fig.2 outline dimensions